

INTEGRATED CIRCUIT HAVING INDEPENDENTLY FORMED  
ARRAY AND PERIPHERAL ISOLATION DIELECTRICS

ABSTRACT OF THE DISCLOSURE

5 The invention comprises a method of forming an integrated circuit, the method comprising: (1) forming a first dielectric layer disposed outwardly from a semiconductor substrate; (2) forming a first intermediate structure outwardly from the a dielectric layer, the first intermediate structure comprising a floating gate layer disposed outwardly from the first dielectric layer, a second dielectric layer disposed outwardly from the floating gate layer, and a first polysilicon layer disposed outwardly from the second dielectric layer; (3) removing regions of the first intermediate structure to form at least one gate stack disposed outwardly from the first dielectric layer; and (4) forming at least one dielectric isolation region after the formation of the gate stacks, wherein the at least one dielectric isolation region is disposed between two gate stacks.

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